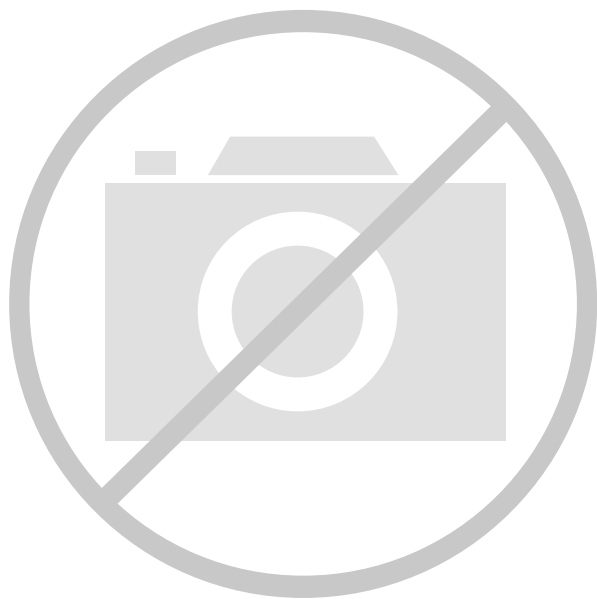




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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 600MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 1143K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1760-BBGA, FCBGA
Supplier Device Package	1760-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu19eg-1ffvd1760e

Table 1: Absolute Maximum Ratings⁽¹⁾ (Cont'd)

Symbol	Description	Min	Max	Units
V _{CCO_PSDDR}	PS DDR I/O supply voltage.	−0.500	1.650	V
V _{CC_PSDDR_PLL}	PS DDR PLL supply voltage.	−0.500	2.000	V
V _{CCO_PSIO}	PS I/O supply.	−0.500	3.630	V
V _{PSIN} ⁽²⁾	PS I/O input voltage.	−0.500	V _{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	−0.500	V _{CCO_PSDDR} + 0.550	V
V _{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	−0.500	2.000	V
Programmable Logic (PL)				
V _{CCINT}	Internal supply voltage.	−0.500	1.000	V
V _{CCINT_IO} ⁽³⁾	Internal supply voltage for the I/O banks.	−0.500	1.000	V
V _{CCAUX}	Auxiliary supply voltage.	−0.500	2.000	V
V _{CCBRAM}	Supply voltage for the block RAM memories.	−0.500	1.000	V
V _{CCO}	Output drivers supply voltage for HD I/O banks.	−0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	−0.500	2.000	V
V _{CCAUX_IO} ⁽⁴⁾	Auxiliary supply voltage for the I/O banks.	−0.500	2.000	V
V _{REF}	Input reference voltage.	−0.500	2.000	V
V _{IN} ⁽²⁾⁽⁵⁾⁽⁷⁾	I/O input voltage for HD I/O banks. ⁽⁶⁾	−0.550	V _{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	−0.550	V _{CCO} + 0.550	V
I _{DC}	Available output current at the pad.	−20	20	mA
I _{RMS}	Available RMS output current at the pad.	−20	20	mA
GTH or GTY Transceiver				
V _{MGTAVCC}	Analog supply voltage for transceiver circuits.	−0.500	1.000	V
V _{MGTAVTT}	Analog supply voltage for transceiver termination circuits.	−0.500	1.300	V
V _{MGTVCCAUX}	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	−0.500	1.900	V
V _{MGTREFCLK}	Transceiver reference clock absolute input voltage.	−0.500	1.300	V
V _{MGTAVTTRCAL}	Analog supply voltage for the resistor calibration circuit of the transceiver column.	−0.500	1.300	V
V _{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	−0.500	1.200	V
I _{DCIN-FLOAT}	DC input current for receiver input pins DC coupled RX termination = floating. ⁽⁸⁾	—	10	mA
I _{DCIN-MGTAVTT}	DC input current for receiver input pins DC coupled RX termination = V _{MGTAVTT} .	—	10	mA
I _{DCIN-GND}	DC input current for receiver input pins DC coupled RX termination = GND. ⁽⁹⁾	—	0	mA
I _{DCIN-PROG}	DC input current for receiver input pins DC coupled RX termination = programmable. ⁽¹⁰⁾	—	0	mA
I _{DCOUT-FLOAT}	DC output current for transmitter pins DC coupled RX termination = floating.	—	6	mA
I _{DCOUT-MGTAVTT}	DC output current for transmitter pins DC coupled RX termination = V _{MGTAVTT} .	—	6	mA

Recommended Operating Conditions

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
Processor System					
V _{CC_PSINTFP} ⁽³⁾	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSINTLP}	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V _{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
V _{CC_PSINTFP_DDR} ⁽³⁾	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V _{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V _{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
V _{PS_MGTRAVCC}	PS-GTR supply voltage.	0.825	0.850	0.875	V
V _{PS_MGTRAVTT}	PS-GTR termination voltage.	1.746	1.800	1.854	V
V _{CCO_PSDDR} ⁽⁴⁾	PS DDR I/O supply voltage.	1.06	–	1.575	V
V _{CC_PSDDR_PLL}	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V _{CCO_PSIO} ⁽⁵⁾	PS I/O supply.	1.710	–	3.465	V
V _{PSIN}	PS I/O input voltage.	–0.200	–	V _{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V _{CCO_PSDDR} + 0.200	
V _{CC_PSBATT} ⁽⁶⁾	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V _{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V _{CCINT_IO} ⁽⁷⁾	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V _{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V _{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V _{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾ (Cont'd)

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V _{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V _{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T _j ⁽¹³⁾	Junction temperature operating range for extended (E) temperature devices. ⁽¹⁴⁾	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

- All voltages are relative to GND.
- For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* ([UG583](#)).
- V_{CC_PSINTFP_DDR} must be tied to V_{CC_PSINTFP}.
- Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
- Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
- If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
- V_{CCINT_IO} must be connected to V_{CCBRAM}.
- Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
- V_{CCAUX_IO} must be connected to V_{CCAUX}.
- The lower absolute voltage specification always applies.
- A total of 200 mA per bank should not be exceeded.
- Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) or *UltraScale Architecture GTY Transceiver User Guide* ([UG578](#)).
- Xilinx recommends measuring the T_j of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* ([UG580](#)). The SYSMON temperature measurement errors (that are described in [Table 69](#) and [Table 124](#)) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted T_j (100°C – 3°C = 97°C).
- Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at T_j = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 6: V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks⁽¹⁾

AC Voltage Overshoot	% of UI at -40°C to 100°C	AC Voltage Undershoot	% of UI at -40°C to 100°C
$V_{CCO} + 0.30$	100%	-0.30	100%
$V_{CCO} + 0.35$	100%	-0.35	90%
$V_{CCO} + 0.40$	100%	-0.40	78%
$V_{CCO} + 0.45$	100%	-0.45	40%
$V_{CCO} + 0.50$	100%	-0.50	24%
$V_{CCO} + 0.55$	100%	-0.55	18.0%
$V_{CCO} + 0.60$	100%	-0.60	13.0%
$V_{CCO} + 0.65$	100%	-0.65	10.8%
$V_{CCO} + 0.70$	92%	-0.70	9.0%
$V_{CCO} + 0.75$	92%	-0.75	7.0%
$V_{CCO} + 0.80$	92%	-0.80	6.0%
$V_{CCO} + 0.85$	92%	-0.85	5.0%
$V_{CCO} + 0.90$	92%	-0.90	4.0%
$V_{CCO} + 0.95$	92%	-0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 7: V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks⁽¹⁾⁽²⁾

AC Voltage Overshoot	% of UI at -40°C to 100°C	AC Voltage Undershoot	% of UI at -40°C to 100°C
$V_{CCO} + 0.30$	100%	-0.30	100%
$V_{CCO} + 0.35$	100%	-0.35	100%
$V_{CCO} + 0.40$	92%	-0.40	92%
$V_{CCO} + 0.45$	50%	-0.45	50%
$V_{CCO} + 0.50$	20%	-0.50	20%
$V_{CCO} + 0.55$	10%	-0.55	10%
$V_{CCO} + 0.60$	6%	-0.60	6%
$V_{CCO} + 0.65$	2%	-0.65	2%
$V_{CCO} + 0.70$	2%	-0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 μ s.

Table 8: V_{PSIN} Maximum Allowed AC Voltage Overshoot and Undershoot for PS I/O Banks⁽¹⁾

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
$V_{CCO_PSIO} + 0.30$	100%	–0.30	100%
$V_{CCO_PSIO} + 0.35$	100%	–0.35	75%
$V_{CCO_PSIO} + 0.40$	100%	–0.40	45%
$V_{CCO_PSIO} + 0.45$	100%	–0.45	40%
$V_{CCO_PSIO} + 0.50$	75%	–0.50	10%
$V_{CCO_PSIO} + 0.55$	75%	–0.55	6%
$V_{CCO_PSIO} + 0.60$	60%	–0.60	2%
$V_{CCO_PSIO} + 0.65$	30%	–0.65	0%
$V_{CCO_PSIO} + 0.70$	20%	–0.70	0%
$V_{CCO_PSIO} + 0.75$	10%	–0.75	0%
$V_{CCO_PSIO} + 0.80$	10%	–0.80	0%
$V_{CCO_PSIO} + 0.85$	8%	–0.85	0%
$V_{CCO_PSIO} + 0.90$	6%	–0.90	0%
$V_{CCO_PSIO} + 0.95$	6%	–0.95	0%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Quiescent Supply Current

Table 9: Typical Quiescent Supply Current⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I _{CCINTQ}	Quiescent V _{CCINT} supply current.	XCZU2	N/A	393	393	344	344	mA
		XCZU3	N/A	393	393	344	344	mA
		XCZU4	719	684	684	601	601	mA
		XCZU5	719	684	684	601	601	mA
		XCZU6	1629	1549	1549	1358	1358	mA
		XCZU7	1263	1201	1201	1055	1055	mA
		XCZU9	1629	1549	1549	1358	1358	mA
		XCZU11	1786	1699	1699	1491	1491	mA
		XCZU15	1987	1890	1890	1660	1660	mA
		XCZU17	2728	2594	2594	2275	2275	mA
		XCZU19	2728	2594	2594	2275	2275	mA
I _{CCINT_IOQ}	Quiescent V _{CCINT_IO} supply current.	XCZU2	N/A	44	44	44	44	mA
		XCZU3	N/A	44	44	44	44	mA
		XCZU4	61	59	59	59	59	mA
		XCZU5	61	59	59	59	59	mA
		XCZU6	61	59	59	59	59	mA
		XCZU7	120	115	115	115	115	mA
		XCZU9	61	59	59	59	59	mA
		XCZU11	120	115	115	115	115	mA
		XCZU15	61	59	59	59	59	mA
		XCZU17	164	158	158	158	158	mA
		XCZU19	164	158	158	158	158	mA
I _{CCOQ}	Quiescent V _{CCO} supply current.	All devices	1	1	1	1	1	mA
I _{CCAUXQ}	Quiescent V _{CCAUX} supply current.	XCZU2	N/A	55	55	55	55	mA
		XCZU3	N/A	55	55	55	55	mA
		XCZU4	90	90	90	90	90	mA
		XCZU5	90	90	90	90	90	mA
		XCZU6	227	227	227	227	227	mA
		XCZU7	174	174	174	174	174	mA
		XCZU9	227	227	227	227	227	mA
		XCZU11	255	255	255	255	255	mA
		XCZU15	266	266	266	266	266	mA
		XCZU17	396	396	396	396	396	mA
		XCZU19	396	396	396	396	396	mA

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: Speed Grade Designations by Device

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$) -1LI ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.72V$)		-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$) -1I ($V_{CCINT} = 0.85V$)
XCZU2EG	-2LE ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$) -1LI ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.72V$)		-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$) -1I ($V_{CCINT} = 0.85V$)
XCZU3CG	-2LE ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$) -1LI ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.72V$)		-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$) -1I ($V_{CCINT} = 0.85V$)
XCZU3EG	-2LE ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$) -1LI ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.72V$)		-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$) -1I ($V_{CCINT} = 0.85V$)
XCZU4CG	-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU4EG	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU4EV	-3E ($V_{CCINT} = 0.90V$), -2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		
XCZU5CG	-2E ($V_{CCINT} = 0.85V$) -2I ($V_{CCINT} = 0.85V$), -2LE ($V_{CCINT} = 0.85V$) -1E ($V_{CCINT} = 0.85V$), -1I ($V_{CCINT} = 0.85V$) -1LI ($V_{CCINT} = 0.85V$) -2LE ($V_{CCINT} = 0.72V$), -1LI ($V_{CCINT} = 0.72V$)		

Table 30: PS DDR Performance (Cont'd)

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR3	All FFV packages, FBVB900 and SFVC784	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1600	664	1600	664	1600	Mb/s
	SFVA625	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1333	664	1333	664	1333	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1066	664	1066	664	1066	Mb/s
DDR3L	All FFV packages, FBVB900 and SFVC784	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single rank component	664	1600	664	1600	664	1600	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1333	664	1333	664	1333	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM ⁽¹⁾⁽²⁾	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM ⁽¹⁾⁽³⁾	664	1066	664	1066	664	1066	Mb/s
LPDDR3	All FFV packages, FBVB900 and SFVC784	Single die package ⁽⁶⁾	664	1600	664	1600	664	1600	Mb/s
		Dual die package ⁽⁶⁾	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single die package ⁽⁶⁾	664	1333	664	1333	664	1333	Mb/s
		Dual die package ⁽⁶⁾	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single die package ⁽⁶⁾	664	1066	664	1066	664	1066	Mb/s
		Dual die package ⁽⁶⁾	664	1066	664	1066	664	1066	Mb/s

Notes:

1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, and UDIMM.
2. Includes: 1 rank 1 slot, dual-die package 2 rank.
3. Includes: 2 rank 1 slot.
4. Dual die package includes single die with ECC.
5. LPDDR4 support is only available as a 32-bit interface.
6. 64-bit LPDDR3 interface performance values are defined without ECC support.

PS Interface Specifications

PS Quad-SPI Controller Interface

Table 41: Generic Quad-SPI Interface⁽¹⁾

Symbol	Description	Load Conditions ⁽²⁾	Min	Max	Units
Quad-SPI device clock frequency operating at 150 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK1}	Quad-SPI clock duty cycle.	15 pF	45	55	%
T _{QSPISSSCLK1}	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
T _{QSPISCLKSS1}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
T _{QSPICKO1}	Clock to output delay, all outputs.	15 pF	2.9	4.5	ns
T _{QSPIDCK1}	Setup time, all inputs.	15 pF	0.9	–	ns
T _{QSPICKD1}	Hold time, all inputs.	15 pF	1.0	–	ns
F _{QSPICLK1}	Quad-SPI device clock frequency.	15 pF	–	150	MHz
F _{QSPIREFCLK1}	Quad-SPI reference clock frequency.	15 pF	–	300	MHz
Quad-SPI device clock frequency operating at 100 MHz. Loopback enabled. LVCMOS 1.8V I/O standard.					
T _{DCQSPICLK2}	Quad-SPI clock duty cycle.	15 pF	45	55	%
		30 pF	45	55	%
T _{QSPISSSCLK2}	Slave select asserted to next clock edge.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPISCLKSS2}	Clock edge to slave select deasserted.	15 pF	5.0	–	ns
		30 pF	5.0	–	ns
T _{QSPICKO2}	Clock to output delay, all outputs.	15 pF	3.2	7.4	ns
		30 pF	3.2	7.4	ns
T _{QSPIDCK2}	Setup time, all inputs.	15 pF	2.3	–	ns
		30 pF	2.3	–	ns
T _{QSPICKD2}	Hold time, all inputs.	15 pF	0.0	–	ns
		30 pF	0.0	–	ns
F _{QSPICLK2}	Quad-SPI device clock frequency.	15 pF	–	100	MHz
		30 pF	–	100	MHz
F _{QSPIREFCLK2}	Quad-SPI reference clock frequency.	15 pF	–	200	MHz
		30 pF	–	200	MHz

Notes:

1. The test conditions are configured for the generic Quad-SPI interface at 150/100 MHz with a 12 mA drive strength and fast slew rate.
2. 30 pF loads are for dual-parallel stacked or stacked modes.

PS I2C Controller Interface

Table 47: I2C Interface⁽¹⁾

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	μs
$T_{I2CFCKH}$	SCL High time.	0.6	–	μs
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	μs
$T_{I2CSCKH}$	SCL High time.	4.0	–	μs
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 78: Input Delay Measurement Methodology (Cont'd)

Description	I/O Standard Attribute	$V_L^{(1)(2)}$	$V_H^{(1)(2)}$	$V_{MEAS}^{(1)(4)(6)}$	$V_{REF}^{(1)(3)(5)}$
SUB_LVDS, 1.8V	SUB_LVDS	0.9 – 0.125	0.9 + 0.125	0 ⁽⁶⁾	–
SLVS, 1.8V	SLVS_400_18	0.9 – 0.125	0.9 + 0.125	0 ⁽⁶⁾	–
SLVS, 2.5V	SLVS_400_25	1.25 – 0.125	1.25 + 0.125	0 ⁽⁶⁾	–
LVPECL, 2.5V	LVPECL	1.25 – 0.125	1.25 + 0.125	0 ⁽⁶⁾	–
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	0.2 – 0.125	0.2 + 0.125	0 ⁽⁶⁾	–
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	0.715 – 0.2	0.715 + 0.2	0 ⁽⁶⁾	–

Notes:

1. The input delay measurement methodology parameters for LVDCI/HSLVDCI are the same for LVCMOS standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H .
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
6. The value given is the differential input voltage.

DSP48 Slice Switching Characteristics

Table 83: DSP48 Slice Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
F _{MAX}	With all registers used.	891	775	645	644	600	MHz
F _{MAX_PATDET}	With pattern detector.	794	687	571	562	524	MHz
F _{MAX_MULT_NOMREG}	Two register multiply without MREG.	635	544	456	440	413	MHz
F _{MAX_MULT_NOMREG_PATDET}	Two register multiply without MREG with pattern detect.	577	492	410	395	371	MHz
F _{MAX_PREADD_NOADREG}	Without ADREG.	655	565	468	453	423	MHz
F _{MAX_NOPIPELINEREG}	Without pipeline registers (MREG, ADREG).	483	410	338	323	304	MHz
F _{MAX_NOPIPELINEREG_PATDET}	Without pipeline registers (MREG, ADREG) with pattern detect.	448	379	314	299	280	MHz

Clock Buffers and Networks

Table 84: Clock Buffers Switching Characteristics

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Global Clock Switching Characteristics (Including BUFGCTRL)							
F _{MAX}	Maximum frequency of a global clock tree (BUFG).	891	775	667	725	667	MHz
Global Clock Buffer with Input Divide Capability (BUFGCE_DIV)							
F _{MAX}	Maximum frequency of a global clock buffer with input divide capability (BUFGCE_DIV).	891	775	667	725	667	MHz
Global Clock Buffer with Clock Enable (BUFGCE)							
F _{MAX}	Maximum frequency of a global clock buffer with clock enable (BUFGCE).	891	775	667	725	667	MHz
Leaf Clock Buffer with Clock Enable (BUFCE_LEAF)							
F _{MAX}	Maximum frequency of a leaf clock buffer with clock enable (BUFCE_LEAF).	891	775	667	725	667	MHz
GTH or GTY Clock Buffer with Clock Enable and Clock Input Divide Capability (BUFG_GT)							
F _{MAX}	Maximum frequency of a serial transceiver clock buffer with clock enable and clock input divide capability.	512	512	512	512	512	MHz

Table 85: MMCM Specification (Cont'd)

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F _{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.

Device Pin-to-Pin Output Parameter Guidelines

The pin-to-pin numbers in Table 87 through Table 89 are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 87: Global Clock Input to Output Delay Without MMCM (Near Clock Region)

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM.								
T _{ICKOF}	Global clock input and output flip-flop <i>without</i> MMCM (near clock region).	XCZU2	N/A	4.90	5.28	5.35	5.61	ns
		XCZU3	N/A	4.90	5.28	5.35	5.61	ns
		XCZU4	4.89	5.83	6.36	6.00	6.79	ns
		XCZU5	4.89	5.83	6.36	6.00	6.79	ns
		XCZU6	5.00	5.91	6.35	6.66	7.09	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.00	5.91	6.35	6.66	7.09	ns
		XCZU11	5.82	6.96	7.61	7.19	8.36	ns
		XCZU15	5.15	6.09	6.55	6.90	7.38	ns
		XCZU17	5.72	6.90	7.40	7.62	8.07	ns
XCZU19	5.72	6.90	7.40	7.62	8.07	ns		

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 88: Global Clock Input to Output Delay Without MMCM (Far Clock Region)

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM.								
T _{ICKOF_FAR}	Global clock input and output flip-flop <i>without</i> MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: Global Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
T _{ICKOFMMCMCC}	Global clock input and output flip-flop <i>with</i> MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
XCZU19	2.44	2.44	2.66	3.19	3.17	ns		

Notes:

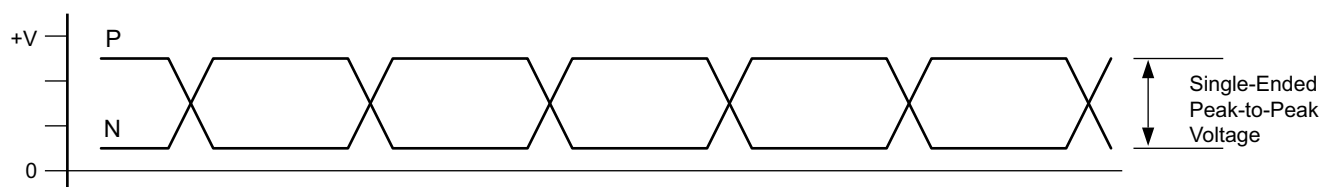
1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 91: Global Clock Input Setup and Hold With MMCM

Symbol	Description	Device	Speed Grade and V _{CCINT} Operating Voltages					Units	
			0.90V	0.85V		0.72V			
			-3	-2	-1	-2	-1		
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
T _{PSMMCMCC_ZU2}	Global clock input and input flip-flop (or latch) with MMCM.	Setup	XCZU2	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU2}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU3}		Setup	XCZU3	N/A	1.83	1.96	2.29	2.48	ns
T _{PHMMCMCC_ZU3}		Hold			−0.19	−0.19	0.13	0.13	ns
T _{PSMMCMCC_ZU4}		Setup	XCZU4	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU4}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU5}		Setup	XCZU5	1.96	1.96	2.10	2.49	2.59	ns
T _{PHMMCMCC_ZU5}		Hold		−0.12	−0.12	−0.12	0.27	0.48	ns
T _{PSMMCMCC_ZU6}		Setup	XCZU6	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU6}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU7}		Setup	XCZU7	1.91	1.91	2.02	2.45	2.70	ns
T _{PHMMCMCC_ZU7}		Hold		−0.14	−0.14	−0.14	0.37	0.38	ns
T _{PSMMCMCC_ZU9}		Setup	XCZU9	1.97	2.00	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU9}		Hold		−0.11	−0.11	−0.11	0.16	0.18	ns
T _{PSMMCMCC_ZU11}		Setup	XCZU11	2.08	2.08	2.23	2.59	2.75	ns
T _{PHMMCMCC_ZU11}		Hold		−0.08	−0.08	0.04	0.35	0.74	ns
T _{PSMMCMCC_ZU15}		Setup	XCZU15	1.96	1.99	2.12	2.26	2.44	ns
T _{PHMMCMCC_ZU15}		Hold		−0.10	−0.10	−0.10	0.17	0.19	ns
T _{PSMMCMCC_ZU17}		Setup	XCZU17	1.89	1.89	2.03	2.36	2.55	ns
T _{PHMMCMCC_ZU17}		Hold		−0.16	−0.16	−0.16	0.31	0.34	ns
T _{PSMMCMCC_ZU19}	Setup	XCZU19	1.89	1.89	2.03	2.36	2.55	ns	
T _{PHMMCMCC_ZU19}	Hold		−0.16	−0.16	−0.16	0.31	0.34	ns	

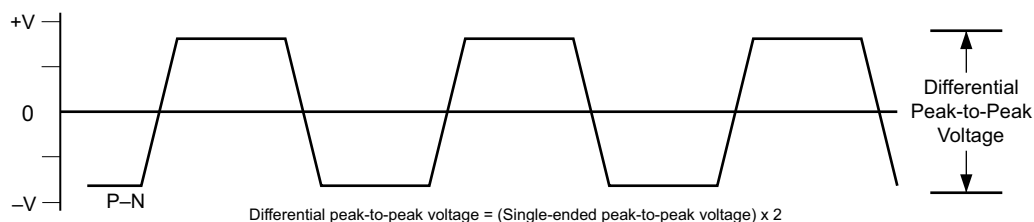
Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.



X16653-101316

Figure 3: Single-Ended Peak-to-Peak Voltage



X16639-101316

Figure 4: Differential Peak-to-Peak Voltage

Table 95 and Table 96 summarize the DC specifications of the GTH transceivers input and output clocks in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* ([UG576](#)) for further details.

Table 95: GTH Transceiver Clock Input Level Specification

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 96: GTH Transceiver Clock Output Level Specification

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N.	$R_T = 100\Omega$ across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N.	$R_T = 100\Omega$ across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage. (P–N), P = High (N–P), N = High	$R_T = 100\Omega$ across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage.	$R_T = 100\Omega$ across P and N signals	300	–	500	mV

Table 115: GTY Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F _{GTYTX}	Serial data rate range		0.500	–	F _{GTYMAX}	Gb/s
T _{RTX}	TX rise time	20%–80%	–	21	–	ps
T _{FTX}	TX fall time	80%–20%	–	21	–	ps
T _{LLSKEW}	TX lane-to-lane skew ⁽¹⁾		–	–	500.00	ps
T _{J32.75}	Total jitter ⁽²⁾⁽⁴⁾	32.75 Gb/s	–	–	0.35	UI
D _{J32.75}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.19	UI
T _{J28.21}	Total jitter ⁽²⁾⁽⁴⁾	28.21 Gb/s	–	–	0.28	UI
D _{J28.21}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J16.375}	Total jitter ⁽²⁾⁽⁴⁾	16.375 Gb/s	–	–	0.28	UI
D _{J16.375}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J15.0}	Total jitter ⁽²⁾⁽⁴⁾	15.0 Gb/s	–	–	0.28	UI
D _{J15.0}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.1 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J14.1}	Total jitter ⁽²⁾⁽⁴⁾	14.025 Gb/s	–	–	0.28	UI
D _{J14.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J13.1}	Total jitter ⁽²⁾⁽⁴⁾	13.1 Gb/s	–	–	0.28	UI
D _{J13.1}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	12.5 Gb/s	–	–	0.28	UI
D _{J12.5_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J12.5_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	12.5 Gb/s	–	–	0.33	UI
D _{J12.5_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J11.3_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	11.3 Gb/s	–	–	0.28	UI
D _{J11.3_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.28	UI
D _{J10.3125_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J10.3125_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	10.3125 Gb/s	–	–	0.33	UI
D _{J10.3125_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_QPLL}	Total jitter ⁽²⁾⁽⁴⁾	9.953 Gb/s	–	–	0.28	UI
D _{J9.953_QPLL}	Deterministic jitter ⁽²⁾⁽⁴⁾		–	–	0.17	UI
T _{J9.953_CPLL}	Total jitter ⁽³⁾⁽⁴⁾	9.953 Gb/s	–	–	0.33	UI
D _{J9.953_CPLL}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J8.0}	Total jitter ⁽³⁾⁽⁴⁾	8.0 Gb/s	–	–	0.32	UI
D _{J8.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.17	UI
T _{J6.6}	Total jitter ⁽³⁾⁽⁴⁾	6.6 Gb/s	–	–	0.30	UI
D _{J6.6}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J5.0}	Total jitter ⁽³⁾⁽⁴⁾	5.0 Gb/s	–	–	0.30	UI
D _{J5.0}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI
T _{J4.25}	Total jitter ⁽³⁾⁽⁴⁾	4.25 Gb/s	–	–	0.30	UI
D _{J4.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.15	UI

Table 115: GTY Transceiver Transmitter Switching Characteristics (Cont'd)

Symbol	Description	Condition	Min	Typ	Max	Units
T _{J3.20}	Total jitter ⁽³⁾⁽⁴⁾	3.20 Gb/s ⁽⁵⁾	–	–	0.20	UI
D _{J3.20}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J2.5}	Total jitter ⁽³⁾⁽⁴⁾	2.5 Gb/s ⁽⁶⁾	–	–	0.20	UI
D _{J2.5}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.10	UI
T _{J1.25}	Total jitter ⁽³⁾⁽⁴⁾	1.25 Gb/s ⁽⁷⁾	–	–	0.15	UI
D _{J1.25}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.06	UI
T _{J500}	Total jitter ⁽³⁾⁽⁴⁾	500 Mb/s ⁽⁸⁾	–	–	0.10	UI
D _{J500}	Deterministic jitter ⁽³⁾⁽⁴⁾		–	–	0.03	UI

Notes:

- Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTY Quad) at maximum line rate.
- Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
- All jitter values are based on a bit-error ratio of 10⁻¹².
- CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
- CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
- CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Integrated Interface Block for 100G Ethernet MAC and PCS

More information and documentation on solutions using the integrated 100 Gb/s Ethernet block can be found at [UltraScale+ Integrated 100G Ethernet MAC/PCS](#). The *UltraScale Architecture and Product Overview (DS890)* lists how many blocks are in each Zynq UltraScale+ MPSoC.

Table 121: Maximum Performance for 100G Ethernet Designs

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2 ⁽¹⁾	-1	-2	-1 ⁽²⁾	
F _{TX_CLK}	Transmit clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{RX_CLK}	Receive clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{RX_SERDES_CLK}	Receive serializer/deserializer clock	390.625	390.625	322.223	322.223	322.223	MHz
F _{DRP_CLK}	Dynamic reconfiguration port clock	250.00	250.00	250.00	250.00	250.00	MHz

Notes:

1. The maximum clock frequency of 390.625 MHz only applies to the CAUI-10 interface. The maximum clock frequency for the CAUI-4 interface is 322.223 MHz.
2. The CAUI-4 interface is not supported by -1L speed grade devices where V_{CCINT}=0.72V.

Integrated Interface Block for PCI Express Designs

More information and documentation on solutions for PCI Express designs can be found at [PCI Express](#). The *UltraScale Architecture and Product Overview (DS890)* lists the Zynq UltraScale+ MPSoCs that include this block.

Table 122: Maximum Performance for PCI Express Designs⁽¹⁾⁽²⁾

Symbol	Description	Speed Grade and V _{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F _{PIPECLK}	Pipe clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
F _{CORECLK}	Core clock maximum frequency.	500.00	500.00	500.00	250.00	250.00	MHz
F _{DRPCLK}	DRP clock maximum frequency.	250.00	250.00	250.00	250.00	250.00	MHz
F _{MCAPCLK}	MCAP clock maximum frequency.	125.00	125.00	125.00	125.00	125.00	MHz

Notes:

1. PCI Express Gen4 operation is supported for x1, x2, x4, and x8 widths.
2. PCI Express Gen4 operation is supported in -3E, -2E, and -2I speed grades.